

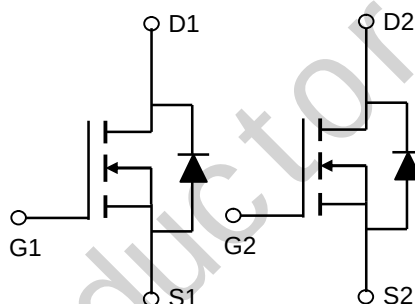
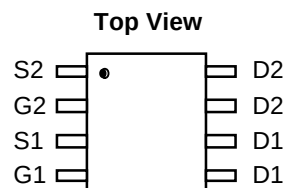
DESCRIPTION

The AM4902N-T1-PF is the N-Channel logic enhancement mode power field effect transistor, is produced using high cell density advanced trench technology.

This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits.

FEATURE

- ◆ 60V/6.3A, $R_{DS(ON)}=30m\Omega$ (typ.)@ $V_{GS}=10V$
- ◆ 60V/5.0A, $R_{DS(ON)}=37m\Omega$ (typ.)@ $V_{GS}=4.5V$
- ◆ Super high design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and Maximum DC current capability
- ◆ Full RoHS compliance
- ◆ SOP8 package design



APPLICATIONS

- ◆ Power Management
- ◆ Portable Equipment
- ◆ DC/DC Converter
- ◆ Load Switch
- ◆ DSC
- ◆ LCD Display inverter

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	6.3	A
$T_A=25^\circ\text{C}$		5	
Pulsed Drain Current ^B	I_{DM}	40	
Power Dissipation	P_D	2	W
$T_A=25^\circ\text{C}$		1.28	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	50	62.5	$^\circ\text{C/W}$	
$t \leq 10s$					
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	73	110	$^\circ\text{C/W}$	
Steady-State					
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	31	40	$^\circ\text{C/W}$	
Steady-State					

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress rating only and functional device operation is not implied

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = 250uA	60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250uA	1.0	1.8	3.0	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48V, V _{GS} =0			1	uA
		V _{DS} = 48V, V _{GS} =0 T _J =55℃			5	
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} = 10V, I _D = 6.3A		30	45	mΩ
		V _{GS} = 4.5V, I _D = 5.0A		37	55	
Source-Drain Diode						
V _{SD}	Diode Forward Voltage	I _S = 1.0A, V _{GS} =0V		0.8	1.3	V
Dynamic Parameters						
Q _g	Total Gate Charge	V _{DS} = 30V V _{GS} = 10V I _D = 5.0A		15.6	16	nC
Q _{gs}	Gate-Source Charge			1.3		
Q _{gd}	Gate-Drain Charge			4.5		
C _{iss}	Input Capacitance	V _{DS} = 25V V _{GS} =0V f=1MHz		520		pF
C _{oss}	Output Capacitance			105		
C _{rss}	Reverse Transfer Capacitance			60		
T _{d(on)}	Turn-On Time	V _{DS} = 30V I _D = 1A V _{GEN} = 10V R _G =6Ω		8	16	nS
T _r				6	12	
T _{d(off)}	Turn-Off Time			25	46	
T _f				4	8	

Note: 1. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

2. Static parameters are based on package level with recommended wire bonding

■ **TYPICAL CHARACTERISTICS** (25 °C Unless Note)

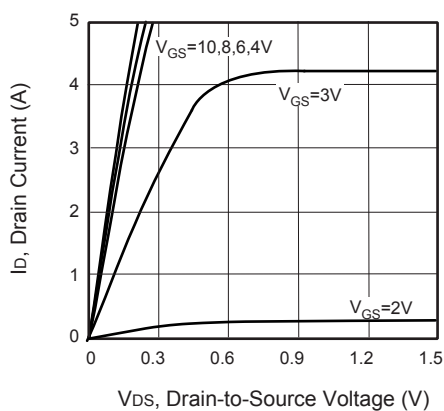


Figure 1. Output Characteristics

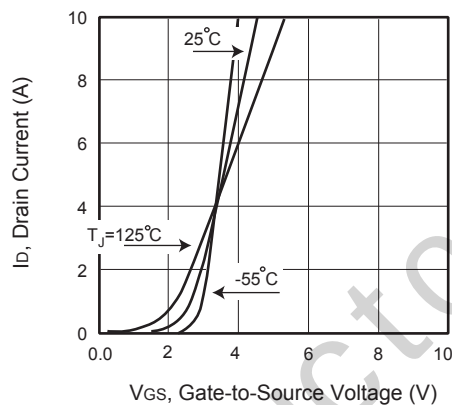


Figure 2. Transfer Characteristics

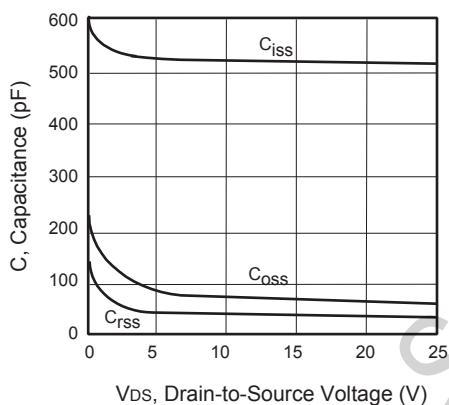


Figure 3. Capacitance

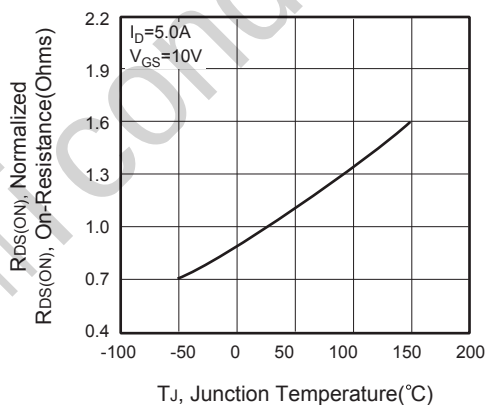


Figure 4. On-Resistance Variation with Temperature

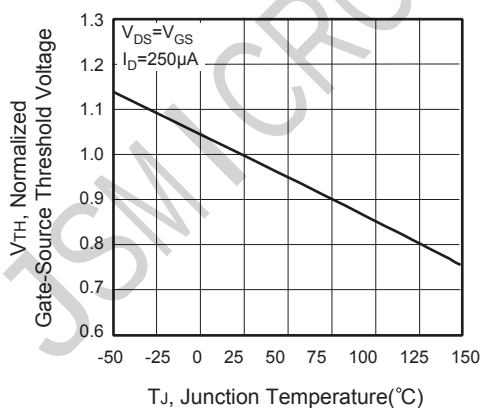


Figure 5. Gate Threshold Variation with Temperature

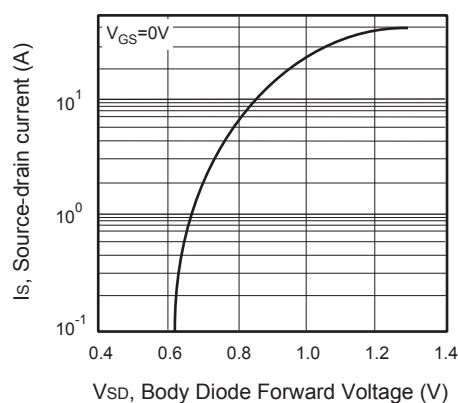


Figure 6. Body Diode Forward Voltage Variation with Source Current

■ TYPICAL CHARACTERISTICS (continuous)

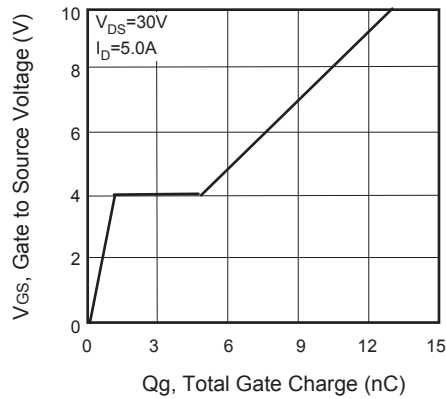


Figure 7. Gate Charge

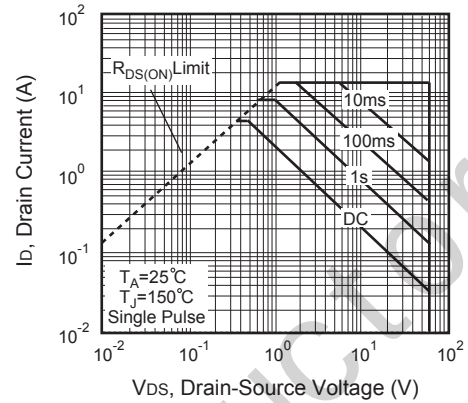


Figure 8. Maximum Safe Operating Area

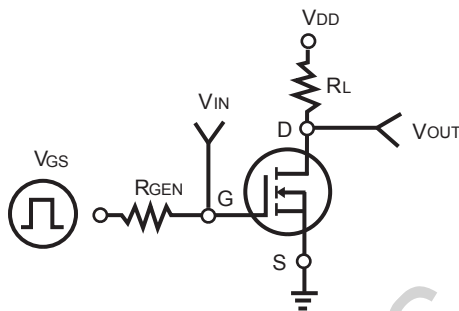


Figure 9. Switching Test Circuit

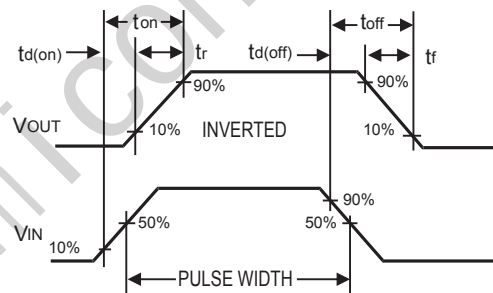


Figure 10. Switching Waveforms

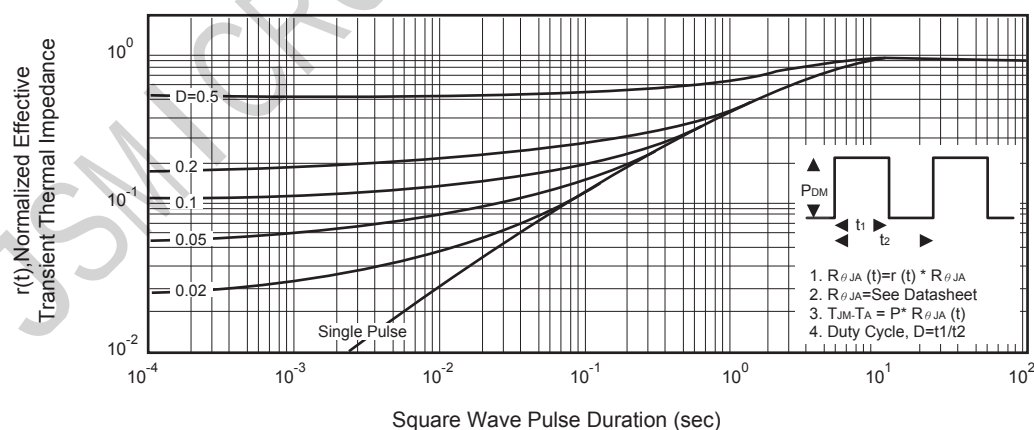
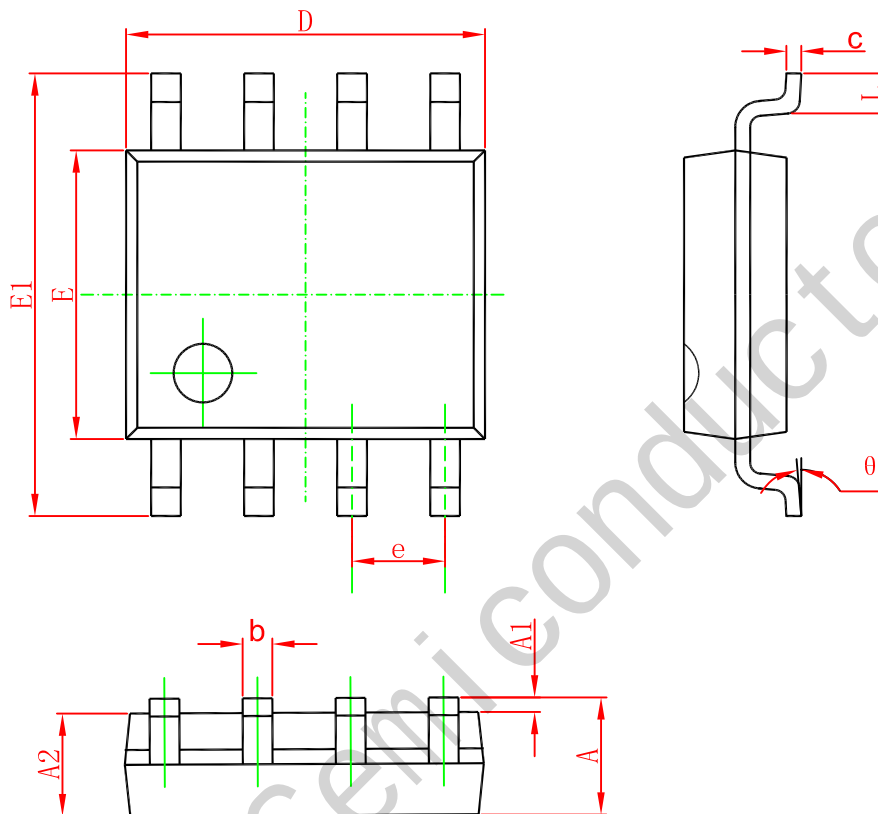


Figure 11. Normalized Thermal Transient Impedance Curve

■ SOP8 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°